

**LISTING OF CLAIMS**

1. (previously presented) A semiconductor device, comprising:

a unitary and non-layered semiconductor substrate comprising a thin portion that is thinner than adjacent portions of the semiconductor substrate, and a recessed portion formed below the thin portion;

wherein the etching rate of the thin portion is slower than that of the surrounding portions of the semiconductor substrate;

at least one through hole is formed in the thin portion that extends from the recessed portion, and entirely through the thin portion to the upper surface of the semiconductor substrate; and

a dopant is infused in at least a portion of the thin portion that is immediately adjacent to the at least one through hole.

Claim 2 (cancelled)

Claim 3 (cancelled)

Claim 4 (original): The semiconductor device set forth in claim 1, wherein the thin portion is formed by means of a selective oxide film.

Claims 5-12 (cancelled)

Claim 13 (previously presented): The semiconductor device set forth in claim 1, wherein the dopant is infused in the entire thin portion.